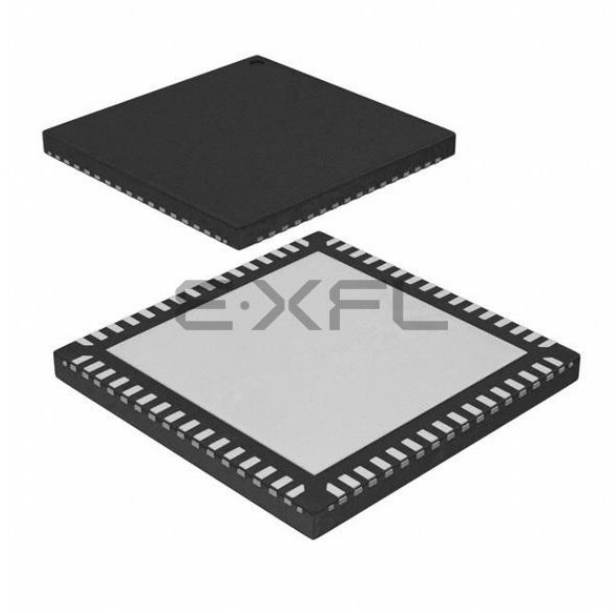
Silicon Labs - EFM32GG11B840F1024IM64-AR Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 16x12b SAR; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg11b840f1024im64-ar

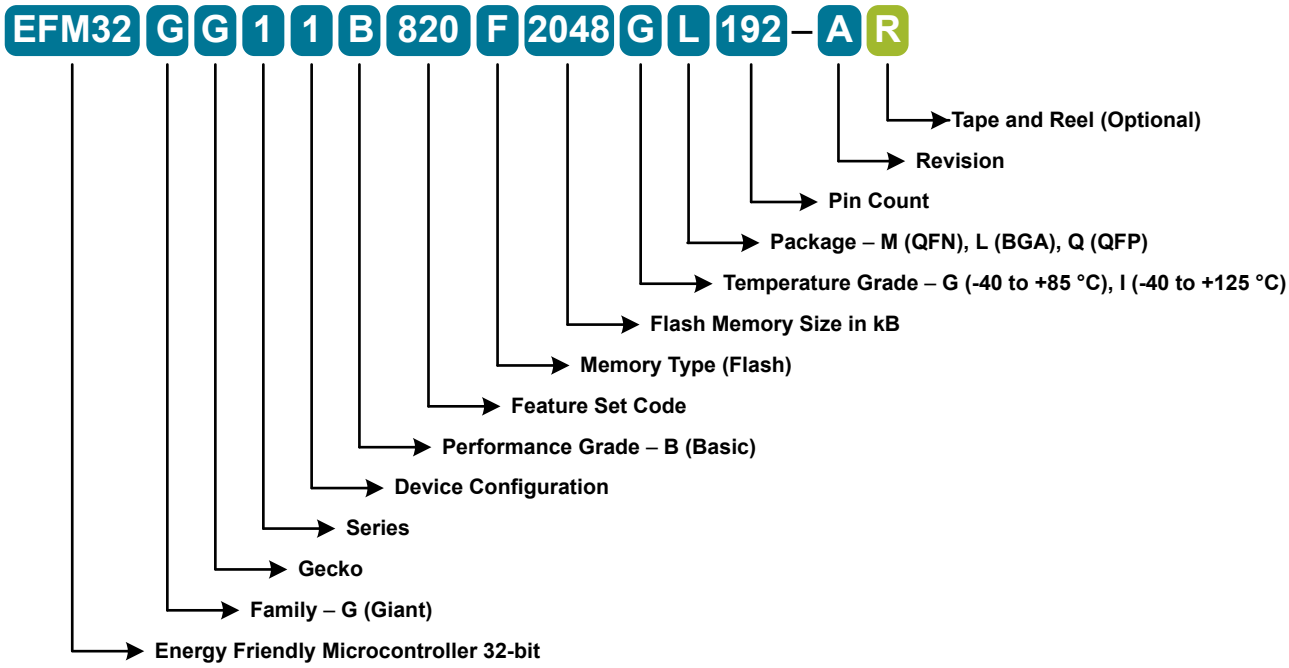

Figure 2.1. Ordering Code Key

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit

Note:

1. The minimum voltage required in bypass mode is calculated using R_{BYP} from the DCDC specification table. Requirements for other loads can be calculated as $V_{DVDD\_min}+I_{LOAD} * R_{BYP\_max}$.
2. VREGVDD must be tied to AVDD. Both VREGVDD and AVDD minimum voltages must be satisfied for the part to operate.
3. The system designer should consult the characteristic specs of the capacitor used on DECOUPLE to ensure its capacitance value stays within the specified bounds across temperature and DC bias.
4. VSCALE0 to VSCALE2 voltage change transitions occur at a rate of 10 mV / usec for approximately 20 usec. During this transition, peak currents will be dependent on the value of the DECOUPLE output capacitor, from 35 mA (with a 1 µF capacitor) to 70 mA (with a 2.7 µF capacitor).
5. When the CSEN peripheral is used with chopping enabled (CSEN_CTRL_CHOPEN = ENABLE), IOVDD must be equal to AVDD.
6. The maximum limit on T_A may be lower due to device self-heating, which depends on the power dissipation of the specific application. T_A (max) = T_J (max) - ($THETA_{JA}$ x PowerDissipation). Refer to the Absolute Maximum Ratings table and the Thermal Characteristics table for T_J and $THETA_{JA}$.

4.1.3 Thermal Characteristics

Table 4.3. Thermal Characteristics

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Thermal resistance, QFN64 Package	$THETA_{JA\_QFN64}$	4-Layer PCB, Air velocity = 0 m/s	—	17.8	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	15.4	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	13.8	—	°C/W
Thermal resistance, TQFP64 Package	$THETA_{JA\_TQFP64}$	4-Layer PCB, Air velocity = 0 m/s	—	33.9	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	32.1	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	30.1	—	°C/W
Thermal resistance, TQFP100 Package	$THETA_{JA\_TQFP100}$	4-Layer PCB, Air velocity = 0 m/s	—	44.1	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	37.7	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	35.5	—	°C/W
Thermal resistance, BGA112 Package	$THETA_{JA\_BGA112}$	4-Layer PCB, Air velocity = 0 m/s	—	42.0	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	37.0	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	35.3	—	°C/W
Thermal resistance, BGA120 Package	$THETA_{JA\_BGA120}$	4-Layer PCB, Air velocity = 0 m/s	—	47.9	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	41.8	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	39.6	—	°C/W
Thermal resistance, BGA152 Package	$THETA_{JA\_BGA152}$	4-Layer PCB, Air velocity = 0 m/s	—	35.7	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	31.0	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	29.5	—	°C/W
Thermal resistance, BGA192 Package	$THETA_{JA\_BGA192}$	4-Layer PCB, Air velocity = 0 m/s	—	47.9	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	41.8	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	39.6	—	°C/W

4.1.12 General-Purpose I/O (GPIO)

Table 4.20. General-Purpose I/O (GPIO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input low voltage	V_{IL}	GPIO pins	—	—	IOVDD*0.3	V
Input high voltage	V_{IH}	GPIO pins	IOVDD*0.7	—	—	V
Output high voltage relative to IOVDD	V_{OH}	Sourcing 3 mA, IOVDD ≥ 3 V, DRIVESTRENGTH[1] = WEAK	IOVDD*0.8	—	—	V
		Sourcing 1.2 mA, IOVDD ≥ 1.62 V, DRIVESTRENGTH[1] = WEAK	IOVDD*0.6	—	—	V
		Sourcing 20 mA, IOVDD ≥ 3 V, DRIVESTRENGTH[1] = STRONG	IOVDD*0.8	—	—	V
		Sourcing 8 mA, IOVDD ≥ 1.62 V, DRIVESTRENGTH[1] = STRONG	IOVDD*0.6	—	—	V
Output low voltage relative to IOVDD	V_{OL}	Sinking 3 mA, IOVDD ≥ 3 V, DRIVESTRENGTH[1] = WEAK	—	—	IOVDD*0.2	V
		Sinking 1.2 mA, IOVDD ≥ 1.62 V, DRIVESTRENGTH[1] = WEAK	—	—	IOVDD*0.4	V
		Sinking 20 mA, IOVDD ≥ 3 V, DRIVESTRENGTH[1] = STRONG	—	—	IOVDD*0.2	V
		Sinking 8 mA, IOVDD ≥ 1.62 V, DRIVESTRENGTH[1] = STRONG	—	—	IOVDD*0.4	V
Input leakage current	I_{IOLEAK}	All GPIO except LFXO pins, GPIO ≤ IOVDD, T ≤ 85 °C	—	0.1	TBD	nA
		LFXO Pins, GPIO ≤ IOVDD, T ≤ 85 °C	—	0.1	TBD	nA
		All GPIO except LFXO pins, GPIO ≤ IOVDD, T > 85 °C	—	—	TBD	nA
		LFXO Pins, GPIO ≤ IOVDD, T > 85 °C	—	—	TBD	nA
Input leakage current on 5VTOL pads above IOVDD	$I_{5VTOLLEAK}$	IOVDD < GPIO ≤ IOVDD + 2 V	—	3.3	TBD	µA
I/O pin pull-up/pull-down resistor	R_{PUD}		TBD	40	TBD	kΩ
Pulse width of pulses removed by the glitch suppression filter	$t_{IOGLITCH}$		15	25	35	ns

4.1.24 USART SPI

SPI Master Timing

Table 4.34. SPI Master Timing

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SCLK period [1] [3] [2]	t_{SCLK}	All USARTs except USART2	2 * $t_{HFPERCLK}$	—	—	ns
		USART2	2 * $t_{HFPERBCLK}$	—	—	ns
CS to MOSI [1] [3]	t_{CS_MO}	USART2, location 4, IOVDD = 1.8 V	-3.2	—	6.8	ns
		USART2, location 4, IOVDD = 3.0 V	-2.3	—	6.0	ns
		USART2, location 5, IOVDD = 1.8 V	-8.1	—	6.3	ns
		USART2, location 5, IOVDD = 3.0 V	-7.3	—	4.4	ns
		All other USARTs and locations, IOVDD = 1.8 V	-15	—	13	ns
		All other USARTs and locations, IOVDD = 3.0 V	-13	—	11	ns
SCLK to MOSI [1] [3]	t_{SCLK_MO}	USART2, location 4, IOVDD = 1.8 V	-0.3	—	9.2	ns
		USART2, location 4, IOVDD = 3.0 V	-0.3	—	8.6	ns
		USART2, location 5, IOVDD = 1.8 V	-3.6	—	5.0	ns
		USART2, location 5, IOVDD = 3.0 V	-3.4	—	3.2	ns
		All other USARTs and locations, IOVDD = 1.8 V	-10	—	11	ns
		All other USARTs and locations, IOVDD = 3.0 V	-9	—	11	ns
MISO setup time [1] [3]	t_{SU_MI}	USART2, location 4, IOVDD = 1.8 V	39.7	—	—	ns
		USART2, location 4, IOVDD = 3.0 V	22.4	—	—	ns
		USART2, location 5, IOVDD = 1.8 V	49.2	—	—	ns
		USART2, location 5, IOVDD = 3.0 V	30.0	—	—	ns
		All other USARTs and locations, IOVDD = 1.8 V	55	—	—	ns
		All other USARTs and locations, IOVDD = 3.0 V	36	—	—	ns

EBI Ready/Wait Timing Requirements

Timing applies to both EBI_REn and EBI_WEn for all addressing modes and both polarities. All numbers are based on route locations 0,1,2 only (with all EBI alternate functions using the same location at the same time). Timing is specified at 10% and 90% of IOVDD, 25 pF external loading, and slew rate for all GPIO set to 6.

Table 4.41. EBI Ready/Wait Timing Requirements

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Setup time, from EBI_ARDY valid to trailing EBI_REn, EBI_WEn edge	t_{SU_ARDY}	IOVDD ≥ 1.62 V	55 + (3 * $t_{HFCOR-ECLK}$)	—	—	ns
		IOVDD ≥ 3.0 V	36 + (3 * $t_{HFCOR-ECLK}$)	—	—	ns
Hold time, from trailing EBI_REn, EBI_WEn edge to EBI_ARDY invalid	t_{H_ARDY}	IOVDD ≥ 1.62 V	-9	—	—	ns

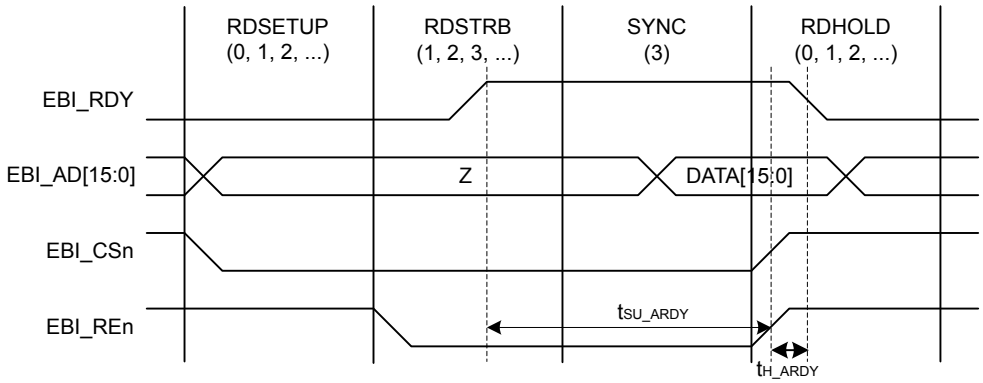

Figure 4.8. EBI Ready/Wait Timing Requirements

MII Receive Timing

Timing is specified with 3.0 V ≤ IOVDD ≤ 3.8 V, 25 pF external loading, and slew rate for all GPIO set to 6 unless otherwise indicated.

Table 4.43. Ethernet MII Receive Timing

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
RX_CLK frequency	F_{RX_CLK}		—	25	—	MHz
RX_CLK duty cycle	DC_{RX_CLK}		35	—	65	%
Setup time, RXD[3:0], RX_DV, RX_ER valid to RX_CLK	t_{SU}		6	—	—	ns
Hold time, RX_CLK to RXD[3:0], RX_DV, RX_ER change	t_{HD}		5	—	—	ns

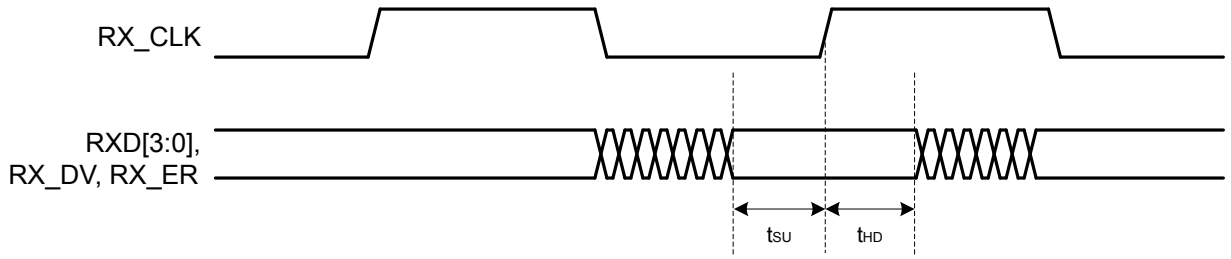

Figure 4.10. Ethernet MII Receive Timing

RMII Transmit Timing

Timing is specified with 3.0 V ≤ IOVDD ≤ 3.8 V, 25 pF external loading, and slew rate for all GPIO set to 6 unless otherwise indicated.

Table 4.44. Ethernet RMII Transmit Timing

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
REF_CLK frequency	F_{REF_CLK}	Output slew rate set to 7	—	50	—	MHz
REF_CLK duty cycle	DC_{REF_CLK}		35	—	65	%
Output delay, REF_CLK to TXD[1:0], TX_EN	t_{OUT}		2.3	—	14.1	ns

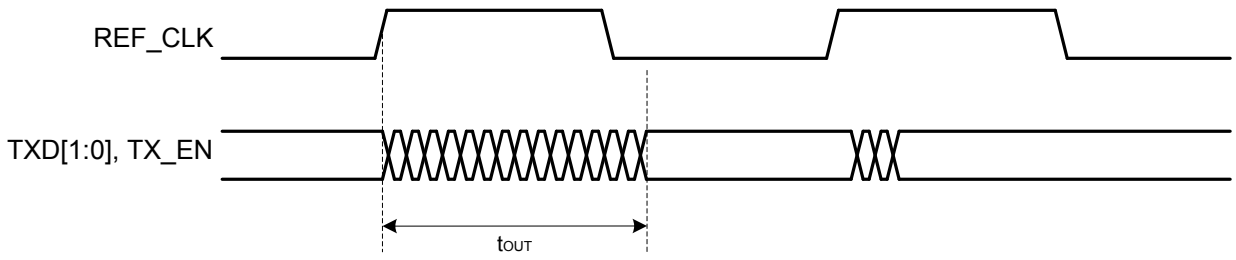

Figure 4.11. Ethernet RMII Transmit Timing

4.1.27 Serial Data I/O Host Controller (SDIO)

SDIO DS Mode Timing

Timing is specified for route location 0 at 3.0 V IOVDD with voltage scaling disabled. Slew rate for SD_CLK set to 6, all other GPIO set to 6, DRIVESTRENGTH = STRONG for all pins. SDIO_CTRL_TXDLYMUXSEL = 1. Loading between 5 and 10 pF on all pins or between 10 and 40 pF on all pins.

Table 4.46. SDIO DS Mode Timing (Location 0)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Clock frequency during data transfer	F_{SD_CLK}	Using HFRCO, AUXHFRCO, or USHFRCO	—	—	23	MHz
		Using HFXO	—	—	TBD	MHz
Clock low time	t_{WL}	Using HFRCO, AUXHFRCO, or USHFRCO	19.7	—	—	ns
		Using HFXO	TBD	—	—	ns
Clock high time	t_{WH}	Using HFRCO, AUXHFRCO, or USHFRCO	19.7	—	—	ns
		Using HFXO	TBD	—	—	ns
Clock rise time	t_R		1.69	3.23	—	ns
Clock fall time	t_F		1.42	2.79	—	ns
Input setup time, CMD, DAT[0:3] valid to SD_CLK	t_{ISU}		6	—	—	ns
Input hold time, SD_CLK to CMD, DAT[0:3] change	t_{IH}		0	—	—	ns
Output delay time, SD_CLK to CMD, DAT[0:3] valid	t_{ODLY}		0	—	14	ns
Output hold time, SD_CLK to CMD, DAT[0:3] change	t_{OH}		5	—	—	ns

4.1.28.2 QSPI DDR Mode

QSPI DDR Mode Timing (Location 0)

Timing is specified with voltage scaling disabled, PHY-mode, route location 0 only, TX DLL = 35, RX DLL = 70, 20-25 pF loading per GPIO, and slew rate for all GPIO set to 6, DRIVESTRENGTH = STRONG.

Table 4.56. QSPI DDR Mode Timing (Location 0)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Half SCLK period	T/2	HFXO	$(1/F_{SCLK})$ * 0.4 - 0.4	—	—	ns
		HFRCO, AUXHFRCO, USHFRCO	$(1/F_{SCLK})$ * 0.44	—	—	ns
Output valid	t_{OV}		—	—	T/2 - 5.0	ns
Output hold	t_{OH}		T/2 - 39.4	—	—	ns
Input setup	t_{SU}		33.1	—	—	ns
Input hold	t_H		-0.9	—	—	ns

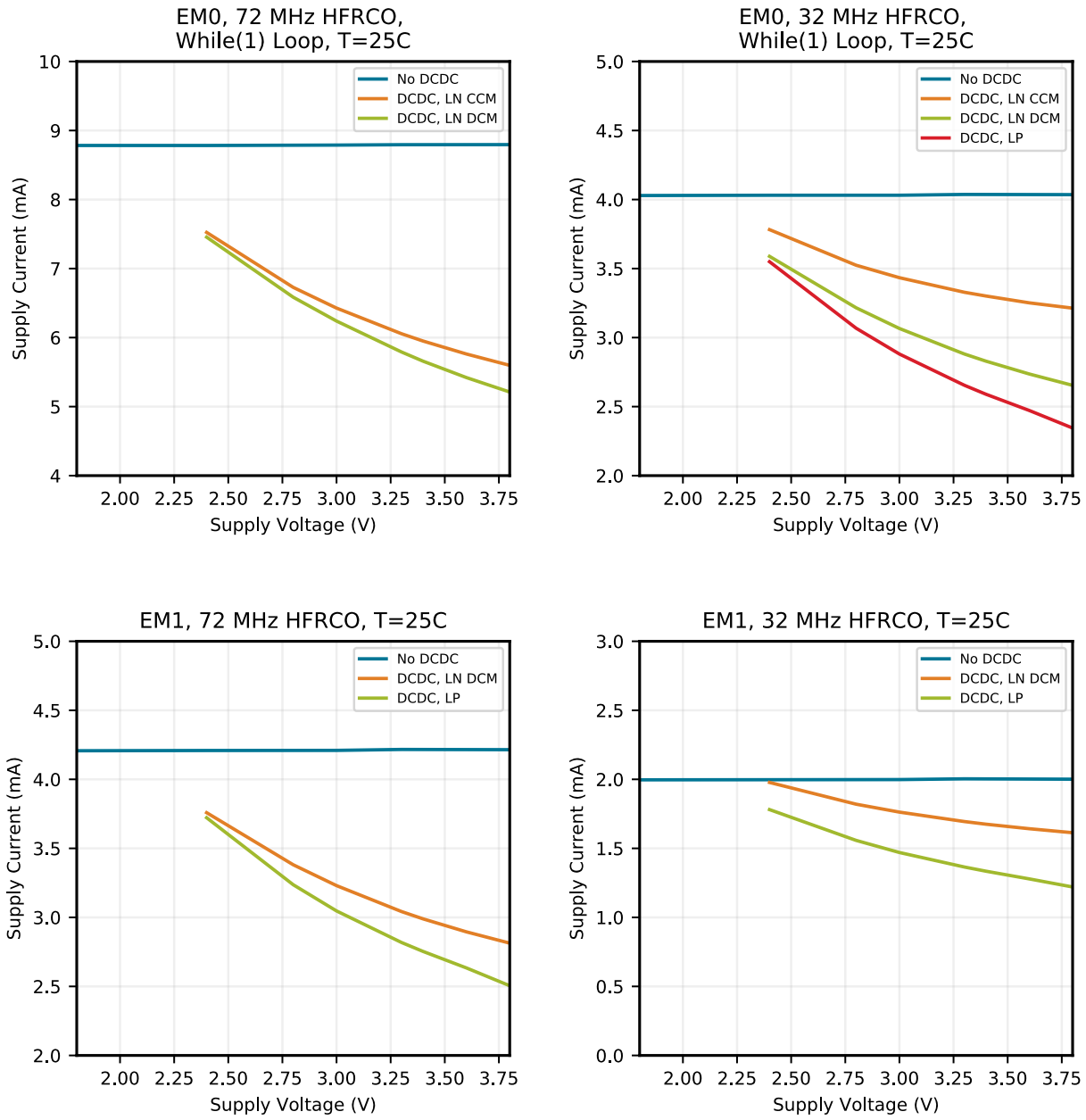

Figure 4.27. EM0 and EM1 Mode Typical Supply Current vs. Supply

Typical supply current for EM2, EM3 and EM4H using standard software libraries from Silicon Laboratories.

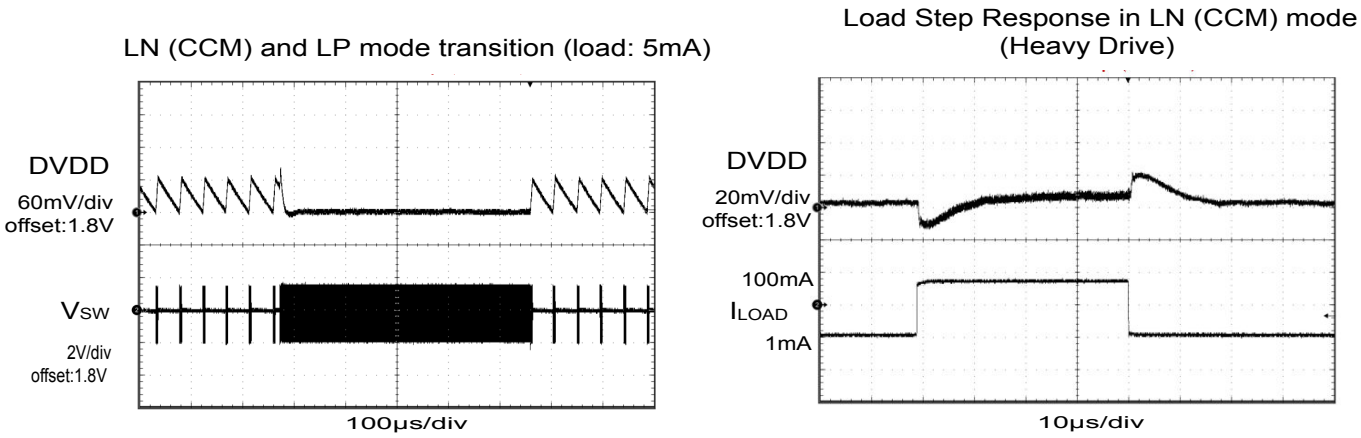

Figure 4.30. DC-DC Converter Transition Waveforms

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PG6	H1	GPIO (5V)	PG7	H2	GPIO (5V)
PG5	H3	GPIO (5V)	PE6	H12	GPIO
PE5	H13	GPIO	DVDD	H14	Digital power supply.
PG9	J1	GPIO (5V)	PG10	J2	GPIO (5V)
PG8	J3	GPIO (5V)	PE3	J12	GPIO
PE4	J13	GPIO	VREGVDD	J14	Voltage regulator VDD input
PG12	K1	GPIO	PG13	K2	GPIO
PG11	K3	GPIO (5V)	PE2	K12	GPIO
PE1	K13	GPIO (5V)	VREGSW	K14	DCDC regulator switching node
PG15	L1	GPIO (5V)	PB15	L2	GPIO (5V)
PG14	L3	GPIO	PC7	L12	GPIO
PE0	L13	GPIO (5V)	VREGVSS	L14	Voltage regulator VSS
PB0	M1	GPIO	PB1	M2	GPIO
PB4	M3	GPIO	PC0	M4	GPIO (5V)
PC3	M5	GPIO (5V)	PA9	M6	GPIO
BODEN	M7	Brown-Out Detector Enable. This pin may be left disconnected or tied to AVDD.	PA12	M8	GPIO (5V)
RESETn	M9	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.	PB10	M10	GPIO (5V)
PD1	M11	GPIO	PC6	M12	GPIO
PD5	M13	GPIO	PD8	M14	GPIO
PB7	N1	GPIO	PB2	N2	GPIO
PB5	N3	GPIO	PC2	N4	GPIO (5V)
PC5	N5	GPIO	PA8	N6	GPIO
PA11	N7	GPIO	PA14	N8	GPIO
PB11	N9	GPIO	PB12	N10	GPIO
PD0	N11	GPIO (5V)	PD2	N12	GPIO (5V)
PD4	N13	GPIO	PD7	N14	GPIO
PB8	P1	GPIO	PB3	P2	GPIO
PB6	P3	GPIO	PC1	P4	GPIO (5V)
PC4	P5	GPIO	PA7	P6	GPIO
PA10	P7	GPIO	PA13	P8	GPIO (5V)
PB9	P9	GPIO (5V)	PB13	P10	GPIO
PB14	P11	GPIO	AVDD	P12	Analog power supply.
PD3	P13	GPIO	PD6	P14	GPIO

5.7 EFM32GG11B3xx in BGA112 Device Pinout

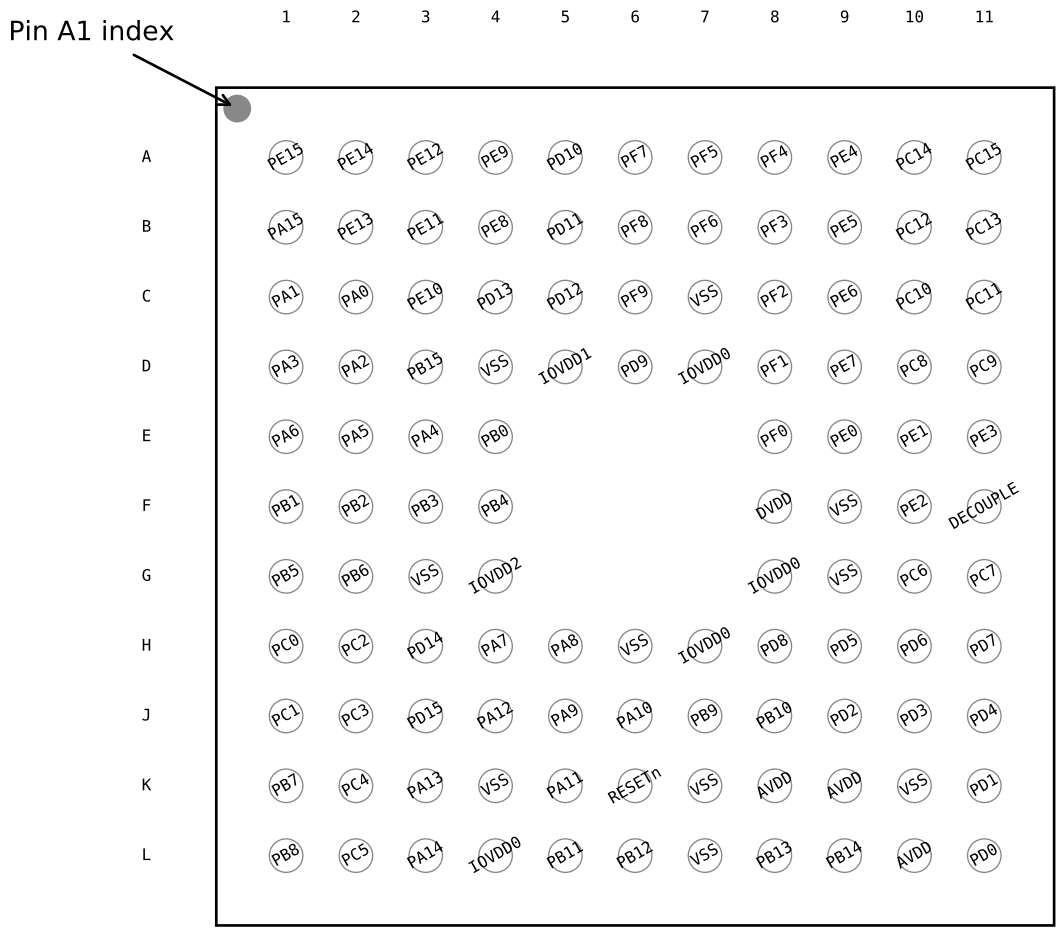

Figure 5.7. EFM32GG11B3xx in BGA112 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.20 GPIO Functionality Table or 5.21 Alternate Functionality Overview.

Table 5.7. EFM32GG11B3xx in BGA112 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE15	A1	GPIO	PE14	A2	GPIO
PE12	A3	GPIO	PE9	A4	GPIO
PD10	A5	GPIO	PF7	A6	GPIO
PF5	A7	GPIO	PF4	A8	GPIO
PE4	A9	GPIO	PC14	A10	GPIO (5V)
PC15	A11	GPIO (5V)	PA15	B1	GPIO
PE13	B2	GPIO	PE11	B3	GPIO

5.15 EFM32GG11B1xx in QFP64 Device Pinout

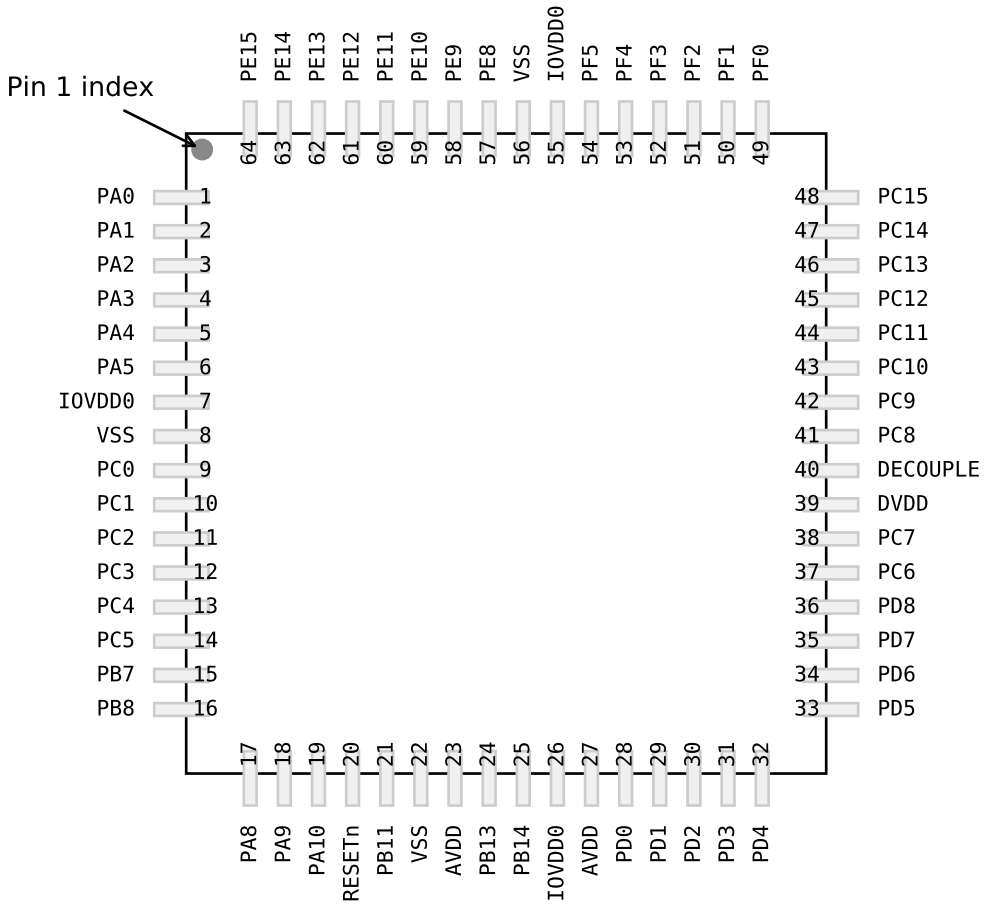

Figure 5.15. EFM32GG11B1xx in QFP64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.20 GPIO Functionality Table or 5.21 Alternate Functionality Overview.

Table 5.15. EFM32GG11B1xx in QFP64 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	PA3	4	GPIO
PA4	5	GPIO	PA5	6	GPIO
IOVDD0	7 26 55	Digital IO power supply 0.	VSS	8 22 56	Ground
PC0	9	GPIO (5V)	PC1	10	GPIO (5V)
PC2	11	GPIO (5V)	PC3	12	GPIO (5V)

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
SDIO_DAT7	0: PD9 1: PB4		SDIO Data 7.
SDIO_WP	0: PF9 1: PC5 2: PB15 3: PB9		SDIO Write Protect.
TIM0_CC0	0: PA0 1: PF6 2: PD1 3: PB6	4: PF0 5: PC4 6: PA8 7: PA1	Timer 0 Capture Compare input / output channel 0.
TIM0_CC1	0: PA1 1: PF7 2: PD2 3: PC0	4: PF1 5: PC5 6: PA9 7: PA0	Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	0: PA2 1: PF8 2: PD3 3: PC1	4: PF2 5: PA7 6: PA10 7: PA13	Timer 0 Capture Compare input / output channel 2.
TIM0_CDTI0	0: PA3 1: PC13 2: PF3 3: PC2	4: PB7	Timer 0 Complimentary Dead Time Insertion channel 0.
TIM0_CDTI1	0: PA4 1: PC14 2: PF4 3: PC3	4: PB8	Timer 0 Complimentary Dead Time Insertion channel 1.
TIM0_CDTI2	0: PA5 1: PC15 2: PF5 3: PC4	4: PB11	Timer 0 Complimentary Dead Time Insertion channel 2.
TIM1_CC0	0: PC13 1: PE10 2: PB0 3: PB7	4: PD6 5: PF2 6: PF13 7: PI6	Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	0: PC14 1: PE11 2: PB1 3: PB8	4: PD7 5: PF3 6: PF14 7: PI7	Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	0: PC15 1: PE12 2: PB2 3: PB11	4: PC13 5: PF4 6: PF15 7: PI8	Timer 1 Capture Compare input / output channel 2.
TIM1_CC3	0: PC12 1: PE13 2: PB3 3: PB12	4: PC14 5: PF12 6: PF5 7: PI9	Timer 1 Capture Compare input / output channel 3.
TIM2_CC0	0: PA8 1: PA12 2: PC8 3: PF2	4: PB6 5: PC2 6: PG8 7: PG5	Timer 2 Capture Compare input / output channel 0.

Port	Bus	CH31	CH30	CH29	CH28	CH27	CH26	CH25	CH24	CH23	CH22	CH21	CH20	CH19	CH18	CH17	CH16	CH15	CH14	CH13	CH12	CH11	CH10	CH9	CH8	CH7	CH6	CH5	CH4	CH3	CH2	CH1	CH0
VDAC0_OUT1 / OPA1_OUT																																	
APORT1Y	BUSAY	PB15		PB13		PB11		PB9				PB5		PB3		PB1		PA15		PA13		PA11		PA9		PA7		PA5		PA3		PA1	
APORT2Y	BUSBY		PB14		PB12		PB10				PB6		PB4		PB2		PB0		PA14		PA12		PA10		PA8		PA6		PA4		PA2		PA0
APORT3Y	BUSCY	PF15		PF13		PF11		PF9		PF7		PF5		PF3		PF1		PE15		PE13		PE11		PE9		PE7		PE5				PE1	
APORT4Y	BUSDY		PF14		PF12		PF10		PF8		PF6		PF4		PF2		PF0		PE14		PE12		PE10		PE8		PE6		PE4				PE0

Table 8.1. BGA120 Package Dimensions

Dimension	Min	Typ	Max
A	0.78	0.84	0.90
A1	0.13	0.18	0.23
A3	0.17	0.21	0.25
A2		0.45 REF	
D		7.00 BSC	
e		0.50 BSC	
E		7.00 BSC	
D1		6.00 BSC	
E1		6.00 BSC	
b	0.20	0.25	0.30
aaa		0.10	
bbb		0.10	
ddd		0.08	
eee		0.15	
fff		0.05	

Note:
1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

8.2 BGA120 PCB Land Pattern

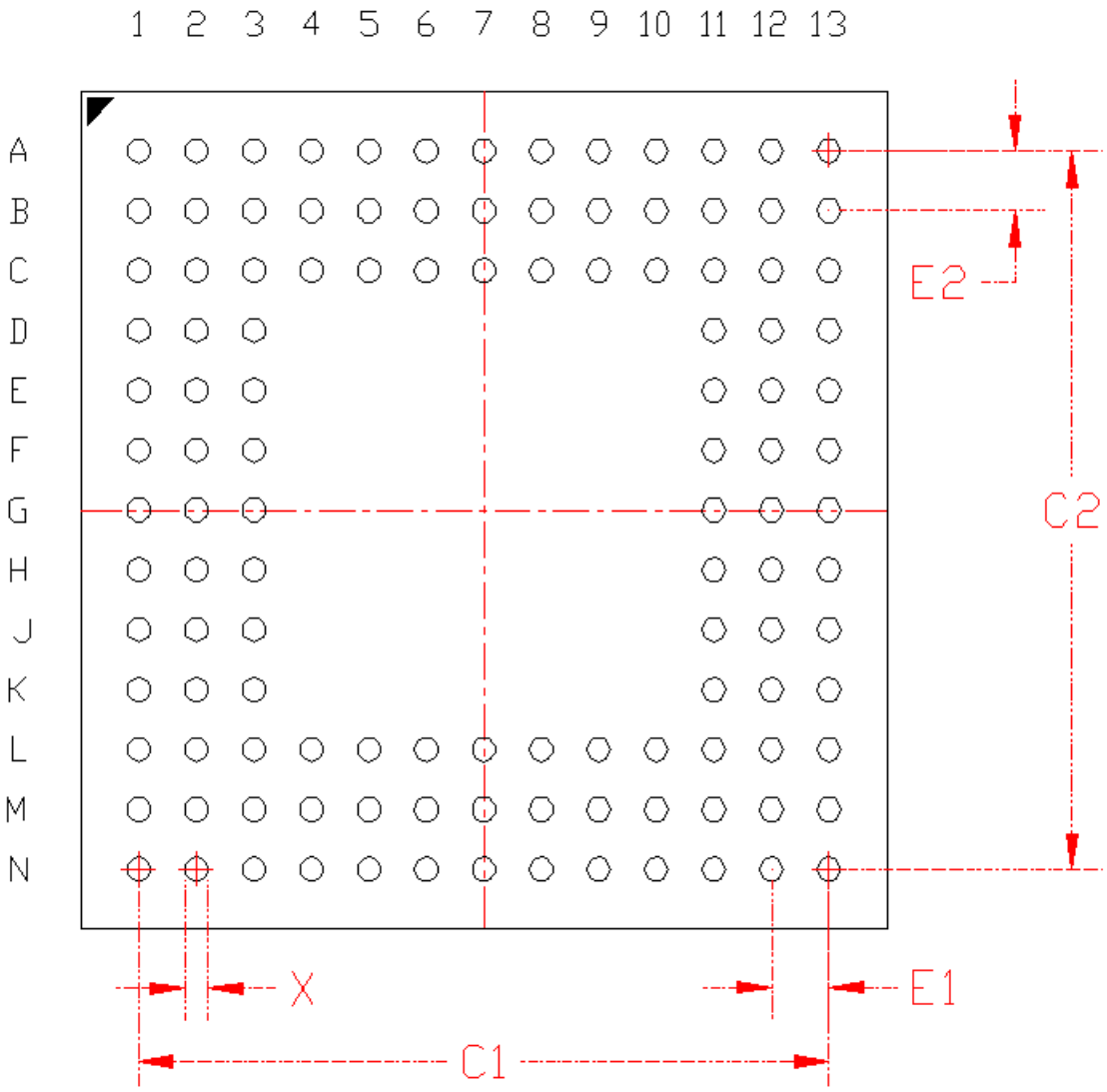

Figure 8.2. BGA120 PCB Land Pattern Drawing

Table 8.2. BGA120 PCB Land Pattern Dimensions

Dimension	Min	Nom	Max
X		0.20	
C1		6.00	
C2		6.00	
E1		0.5	
E2		0.5	

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing is per the ANSI Y14.5M-1994 specification.
3. This Land Pattern Design is based on the IPC-7351 guidelines.
4. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
5. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
6. The stencil thickness should be 0.125 mm (5 mils).
7. The ratio of stencil aperture to land pad size should be 1:1.
8. A No-Clean, Type-3 solder paste is recommended.
9. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

9.3 BGA112 Package Marking

Figure 9.3. BGA112 Package Marking

The package marking consists of:

- PPPPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code. The first letter is the device revision.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.

Table 10.2. TQFP100 PCB Land Pattern Dimensions

Dimension	Min	Nom	Max
C1		15.4	
C2		15.4	
E		0.50 BSC	
X		0.30	
Y		1.50	

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
5. The stencil thickness should be 0.125 mm (5 mils).
6. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads.
7. A No-Clean, Type-3 solder paste is recommended.
8. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

10.3 TQFP100 Package Marking

Figure 10.3. TQFP100 Package Marking

The package marking consists of:

- PPPPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code. The first letter is the device revision.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.